

IRF9540NPbF

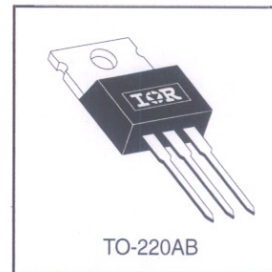
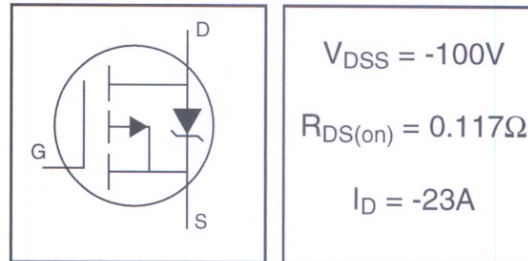
- Lead-Free
- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- P-Channel
- Fully Avalanche Rated

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

HEXFET® Power MOSFET



Absolute Maximum Ratings

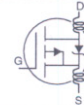
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}$	-23	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}$	-16	
I_{DM}	Pulsed Drain Current ①	-76	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	140	W
	Linear Derating Factor	0.91	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	430	mJ
I_{AR}	Avalanche Current ①	-11	A
E_{AR}	Repetitive Avalanche Energy ①	14	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.1	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-100	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.11	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.117	Ω	$V_{GS} = -10V, I_D = -11A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	5.3	—	—	S	$V_{DS} = -50V, I_D = -11A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-25	μA	$V_{DS} = -100V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	97	nC	$I_D = -11A$
Q_{gs}	Gate-to-Source Charge	—	—	15		$V_{DS} = -80V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	51		$V_{GS} = -10V$, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	15	—		$V_{DD} = -50V$
t_r	Rise Time	—	67	—	ns	$I_D = -11A$
$t_{d(off)}$	Turn-Off Delay Time	—	51	—		$R_G = 5.1\Omega$
t_f	Fall Time	—	51	—		$R_D = 4.2\Omega$, See Fig. 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{ISS}	Input Capacitance	—	1300	—	pF	$V_{GS} = 0V$
C_{OSS}	Output Capacitance	—	400	—		$V_{DS} = -25V$
C_{RSS}	Reverse Transfer Capacitance	—	240	—		$f = 1.0\text{MHz}$, See Fig. 5



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-23	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-76		
V_{SD}	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -1\text{A}, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	150	220	ns	$T_J = 25^\circ\text{C}, I_F = -11A$
Q_{rr}	Reverse Recovery Charge	—	830	1200	nC	$di/dt = -100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting $T_J = 25^\circ\text{C}$, $L = 7.1\text{mH}$
 $R_G = 25\Omega, I_{AS} = -11A$. (See Figure 12)

③ $I_{SD} \leq -11A, di/dt \leq -470A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$

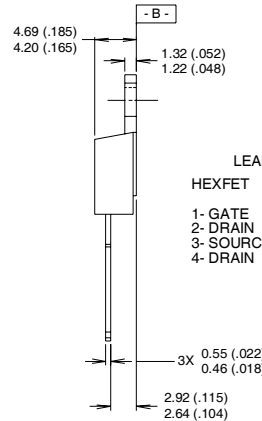
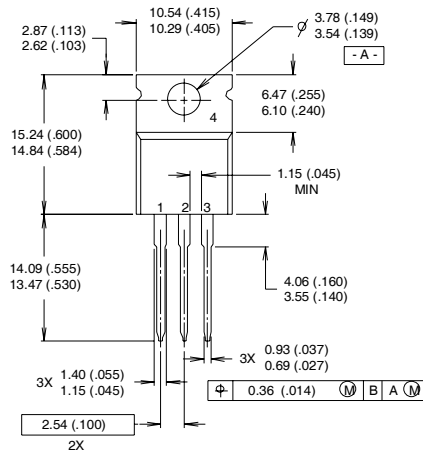
④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

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TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK
1- GATE	1- GATE
2- DRAIN	2- COLLECTOR
3- SOURCE	3- EMITTER
4- DRAIN	4- COLLECTOR

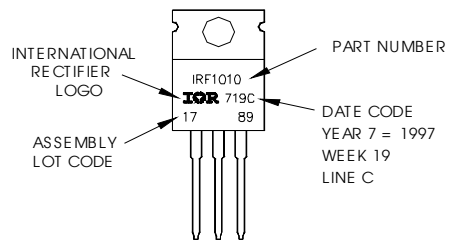
NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line
 position indicates "Lead-Free"



Data and specifications subject to change without notice.

